

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	325	438/28,81.cccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/31 11:27
S1	15259	((257/79) or (438/29) or (438/33) or (438/81) or (438/271) or (438/622) or (438/623) or (438/689-692) or (438/700) or (438/701) or (438/713)).CCCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2007/10/02 08:25
S2	929201	led or (light\$1emitting\$1diode) or (light adj emitting adj diode) or (light\$1emitting adj diode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:26
S3	281	((surface adj emit\$3) or (surface\$1emit\$3)) adj diode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:46
S4	2478370	((crystal adj growth) or (crystal\$1growth)) with plane or substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:47
S5	3622	reflection adj plane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:48
S6	2544	output adj plane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:48

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S7	762213	etch\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:49
S9	826	(taper\$3) adj plane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:50
S10	31510	(v\$1shape\$2 or (v adj shape\$2)) adj groove	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:52
S11	110375	AlGaN or SiC	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:53
S12	228615	dic\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:53
S13	232664	blast\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:53
S14	187473	(metal adj layer) or (metal\$1layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:54

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S15	5614680	group III nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:54
S16	2	polished adj conductive adj substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:55
S17	22344	dry adj etch	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 08:55
S18	442	luminous adj wavelength	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:07
S19	2804	(polish\$3) adj treatment	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:09
S21	104	S2 and S3 and S4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:15
S22	1949	S4 and (S5 or S6)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:11

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S23	1	S21 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:11
S24	6707374	shaping process	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:15
S25	492814	semiconductor with layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:37
S26	138	S2 and S3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:37
S27	361572	S4 and S25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:38
S28	49	S26 and S27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:48
S29	2640183	taper plane	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:48

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S30	209556	S2 and S29	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 09:49
S31	7	(crystal adj growth adj plane) with (crystal adj growth adj substrate)	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 11:44
S32	2460	S1 and S2	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 11:45
S33	2253	S32 and S4	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 11:45
S34	10	S33 and S3	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 12:51
S35	8	"5563900"	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 12:57
S36	3	"5151756"	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/10/02 12:57

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S37	8	"5563900"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/25 08:30
S38	32	"4675058"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/25 09:03
S39	86	"5684309"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/25 10:24
S40	2	"20060273324"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/25 13:45
S41	3	(surface\$1emitt\$3) same light\$1emitting\$1diode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/31 06:37
S42	8	(surface\$1emitt\$3) and light\$1emitting\$1diode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/31 06:37
S43	965867	led or (light\$1emitting\$1diode) or (light adj emitting adj diode) or (light\$1emitting adj diode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2008/03/31 06:40

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S44	2591600	((crystal adj growth) or (crystal\$1growth)) with plane or substrate	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2008/03/31 06:40
S45	32100	(v\$1shape\$2 or (v adj shape\$2)) adj groove	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2008/03/31 06:40
S46	897	S43 and S44 and S45	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/31 06:40
S47	206	S46 and damage	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/31 06:42
S48	60	S46 and quantum adj well	US-PCPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2008/03/31 06:45